

Description

The 20P06S is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 20P06S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

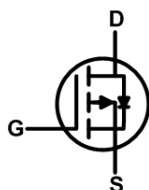
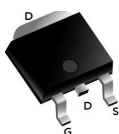
Super Low Gate Charge

100% EAS Guaranteed

Green Device Available

Excellent CdV/dt effect decline

Advanced high cell density Trench technology

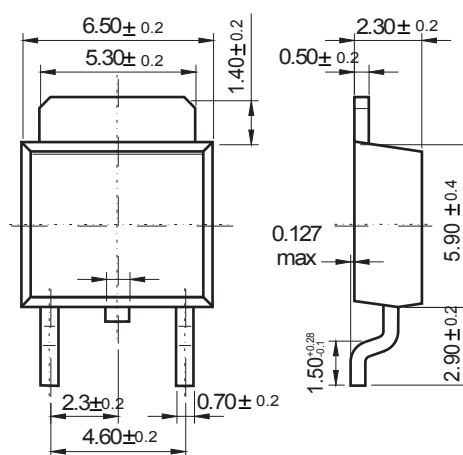


Product Summary

BVDSS	RDSON	ID
-60V	80mΩ	-18A

TO-252

Unit: mm



Dimensions in inches and (millimeters)

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-18	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-8.8	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-2.8	A
I_{DM}	Pulsed Drain Current ²	-25	A
EAS	Single Pulse Avalanche Energy ³	20	mJ
I_{AS}	Avalanche Current	-20	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	25	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	5	$^\circ C/W$

20P06S

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.049	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-8A$	---	80	97	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-6A$	---	97	126	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	5.42	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=150^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-5A$	---	5.8	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V$, $V_{GS}=-4.5V$, $I_D=-5A$	---	5.85	---	nC
Q_{gs}	Gate-Source Charge		---	2.9	---	
Q_{gd}	Gate-Drain Charge		---	1.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-12V$, $V_{GS}=-10V$, $R_G=3.3\Omega$, $I_D=-5A$	---	10	---	ns
T_r	Rise Time		---	17	---	
$T_{d(off)}$	Turn-Off Delay Time		---	22	---	
T_f	Fall Time		---	21	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $F=1MHz$	---	715	---	pF
C_{oss}	Output Capacitance		---	51	---	
C_{rss}	Reverse Transfer Capacitance		---	34	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-9.5	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-24	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-8A$, $dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	10.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	5.4	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD}=-25V$, $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-15A$
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

RATING AND CHARACTERISTIC CURVES (20P06S)

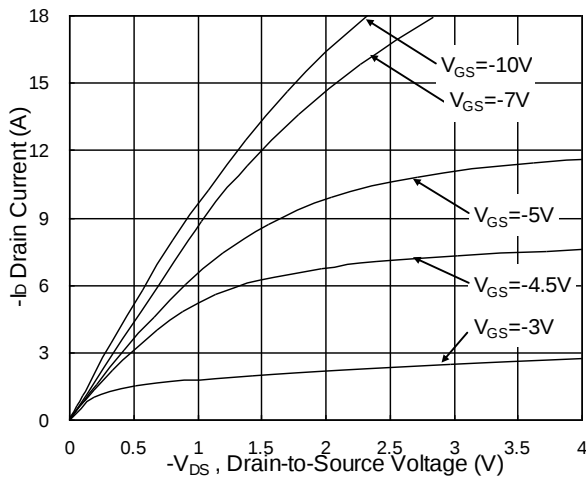


Fig.1 Typical Output Characteristics

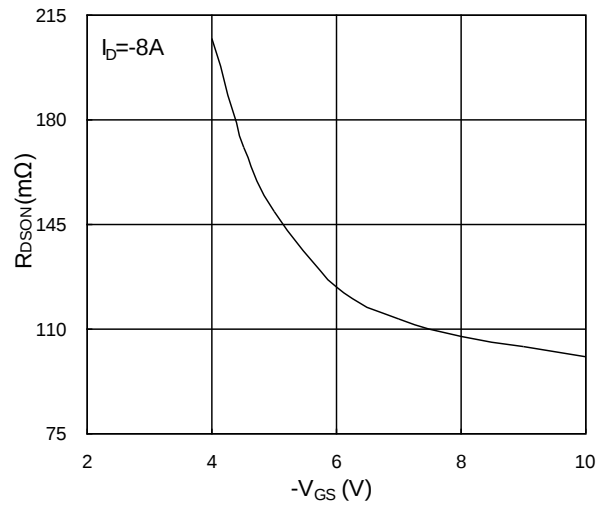


Fig.2 On-Resistance vs. G-S Voltage

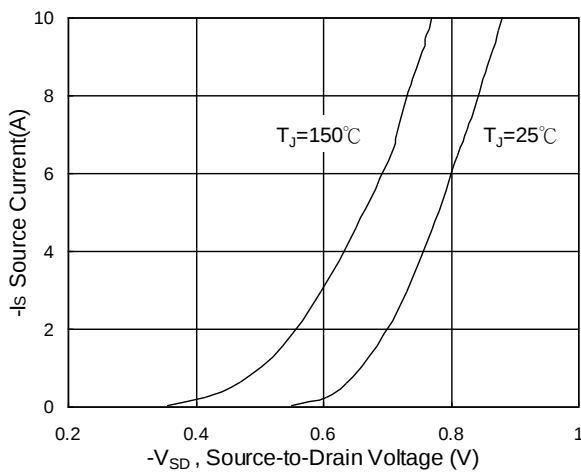


Fig.3 Forward Characteristics Of Reverse

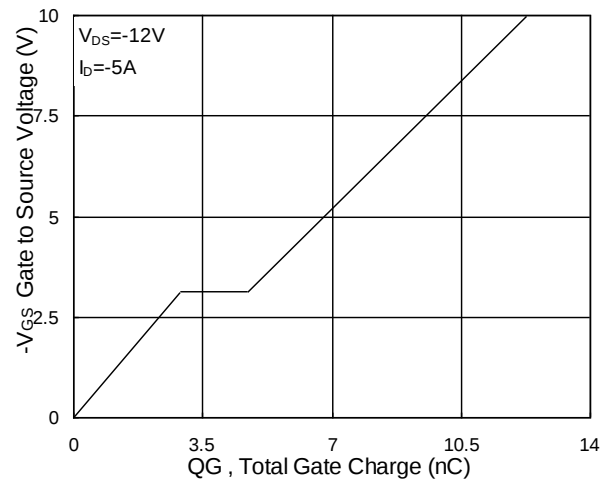


Fig.4 Gate-Charge Characteristics

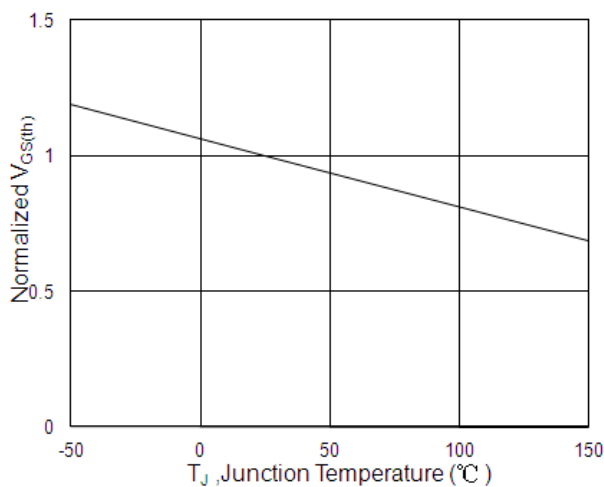


Fig.5 Normalized $V_{GS(th)}$ vs. T_j

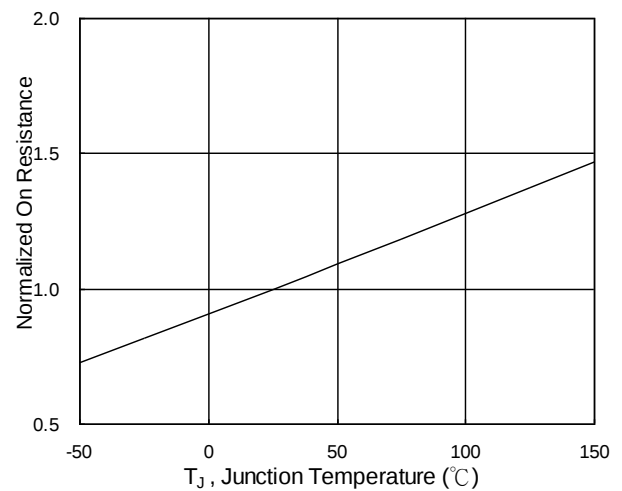


Fig.6 Normalized $R_{DS(on)}$ vs. T_j

RATING AND CHARACTERISTIC CURVES (20P06S)

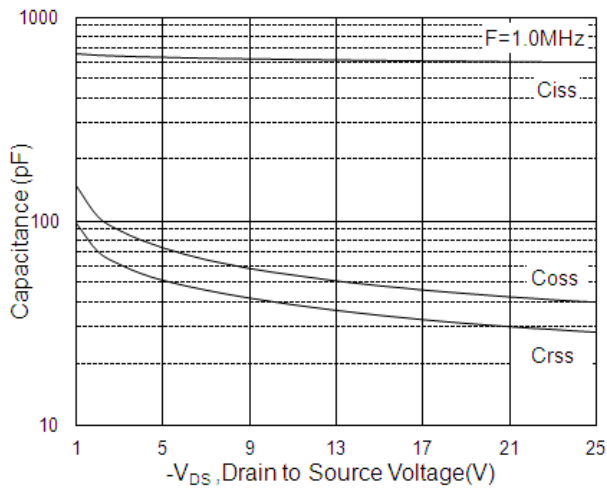


Fig.7 Capacitance

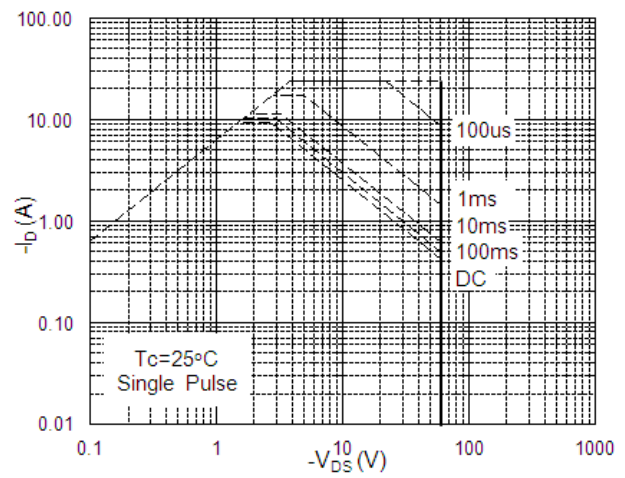


Fig.8 Safe Operating Area

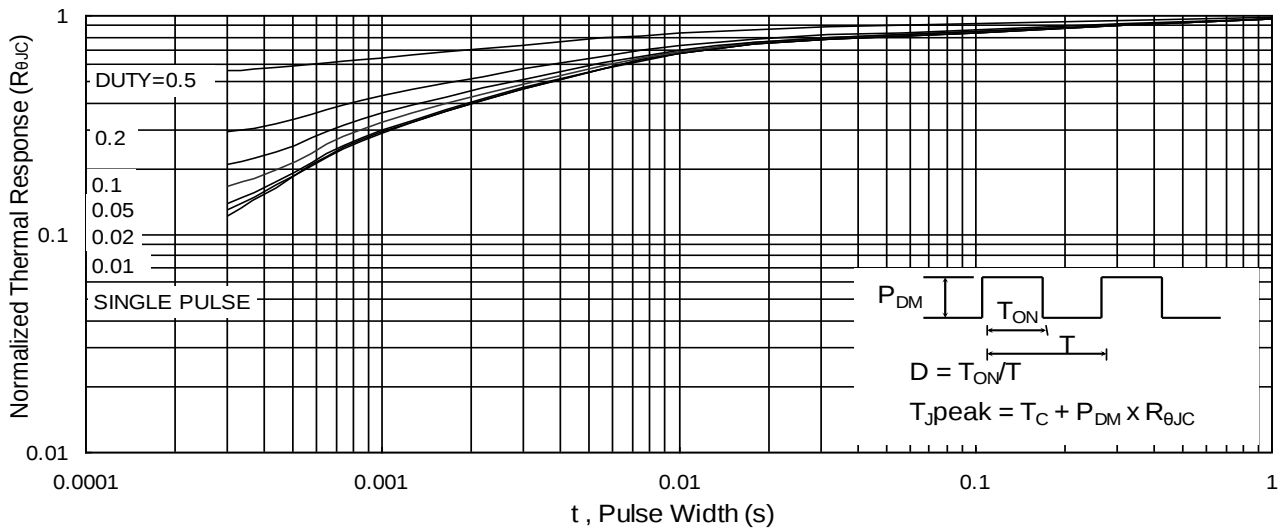


Fig.9 Normalized Maximum Transient Thermal Impedance

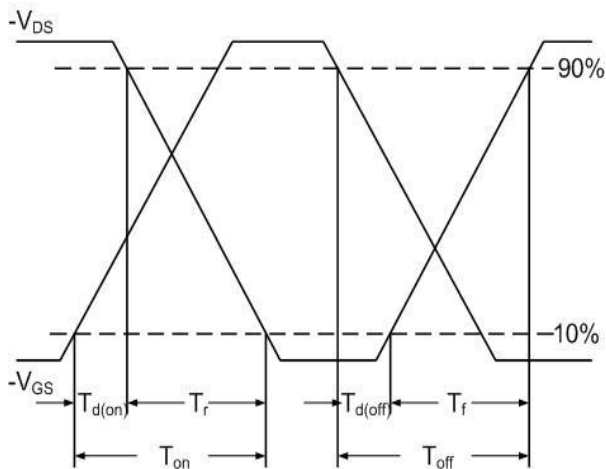


Fig.10 Switching Time Waveform

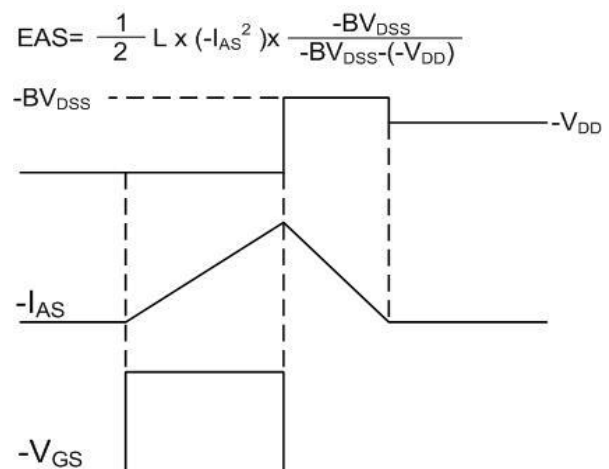


Fig.11 Unclamped Inductive Switching Waveform